



《风光欣》技术资料

2SC3265

NPN EPITAXIAL SILICON TRANSISTOR

*Features

High $h_{FE}=160\sim 320$

Low Collector Saturation Voltage

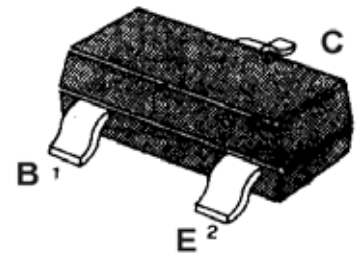
$V_{CE(sat)}=0.5V(\text{Max.})$ $I_C=500mA, I_B=20mA$

Complementary Pair With 2SA1298

ABSOLUTE MAXIMUM RATINGS($T_A=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter -Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Collector Dissipation	P_C	225	mW
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~150	

SOT-23



ELECTRICAL CHARACTERISTICS ($T_A=25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=500\mu A, I_E=0$	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA, I_B=0$	25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=50\mu A, I_C=0$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=35V, I_E=0$			100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=6V, I_C=0$			100	nA
DC Current Gain	h_{FE}	$V_{CE}=1V, I_C=50mA$	160		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=20mA$			0.5	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=10mA$		120		MHz
Collector Output Capacitance	C_{ob}	$f=1MHz, V_{CB}=10V, I_E=0$		13		pF

DEVICE MARKING : KEY